

V_{DSS}	45V
$R_{DS(on)}(Max.)$	100mΩ
I_D	±2.5A
P_D	0.54W

●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).
- 4) Pb-free lead plating ; RoHS compliant

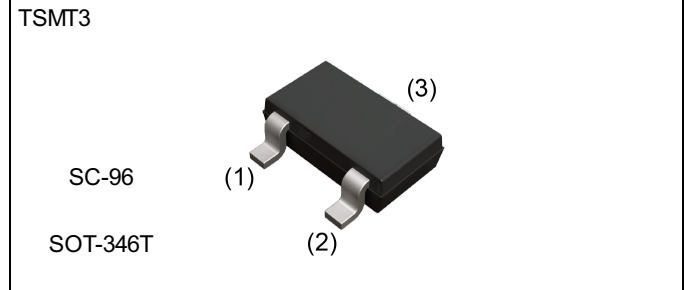
●Application

DC/DC converters, Relay drive

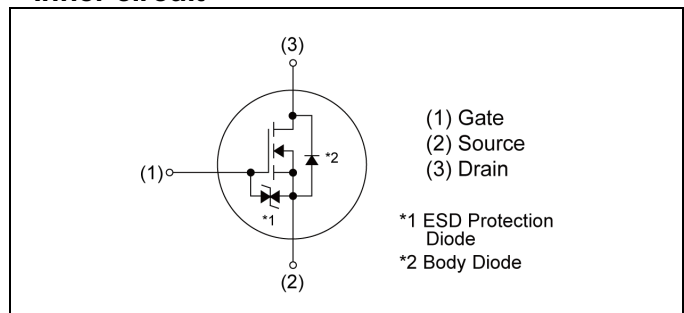
●Absolute maximum ratings ($T_a = 25^{\circ}C$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	45	V
Continuous drain current	I_D^{*1}	±2.5	A
Pulsed drain current	$I_{D,pulse}^{*2}$	±10	A
Gate - Source voltage	V_{GSS}	±20	V
Avalanche energy, single pulse	E_{AS}^{*3}	4.8	mJ
Power dissipation	P_D^{*4}	0.54	W
	P_D^{*5}	1	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Outline



●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TL
	Marking	ZF

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*4}	-	-	125	°C/W
	R_{thJA}^{*5}	-	-	231	°C/W

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	45	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	42	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 45V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	3.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-4.2	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*6}$	$V_{GS} = 10V, I_D = 2.5A$	-	70	100	mΩ
		$V_{GS} = 4.5V, I_D = 2.5A$	-	95	150	
		$V_{GS} = 4V, I_D = 2.5A$	-	105	160	
		$V_{GS} = , I_D =$	-	-	-	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	7	-	Ω
Forward Transfer Admittance	$ Y_{fs} ^{*6}$	$V_{DS} = 10V, I_D = 2.5A$	2	4.2	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*3 $L \approx 1\mu H$, $V_{DD} = 25V$, $R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$

*4 Mounted on a ceramic board (30×30×0.8mm)

*5 Mounted on a FR4 (12×20×0.8mm)

*6 Pulsed

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	260	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	90	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	30	-	
Turn - on delay time	$t_{d(on)}^{*6}$	$V_{DD} \approx 25V, V_{GS} = 10V$	-	9	-	ns
Rise time	t_r^{*6}	$I_D = 1.25A$	-	11	-	
Turn - off delay time	$t_{d(off)}^{*6}$	$R_L \approx 20\Omega$	-	25	-	
Fall time	t_f^{*6}	$R_G = 10\Omega$	-	8	-	

●Gate charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions		Values			Unit
				Min.	Typ.	Max.	
Total gate charge	Q_g^{*6}	$V_{DD} \approx 25V$ $I_D = 2.5A$	$V_{GS} = 10V$	-	6	12	nC
Gate - Source charge	Q_{gs}^{*6}		$V_{GS} = 5V$	-	3.6	-	
Gate - Drain charge	Q_{gd}^{*6}			-	1.5	-	
				-	0.8	-	

●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_a = 25^\circ\text{C}$	-	-	0.8	A
Forward voltage	V_{SD}^{*6}	$V_{GS} = 0V, I_S = 2.5A$	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

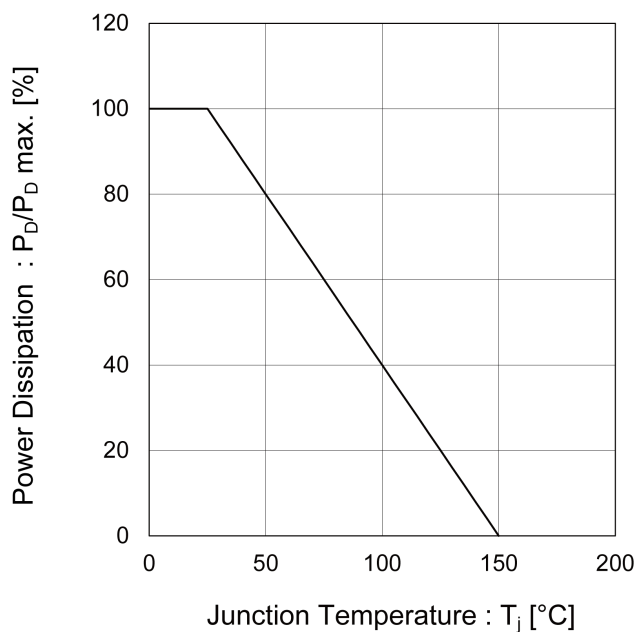


Fig.2 Maximum Safe Operating Area

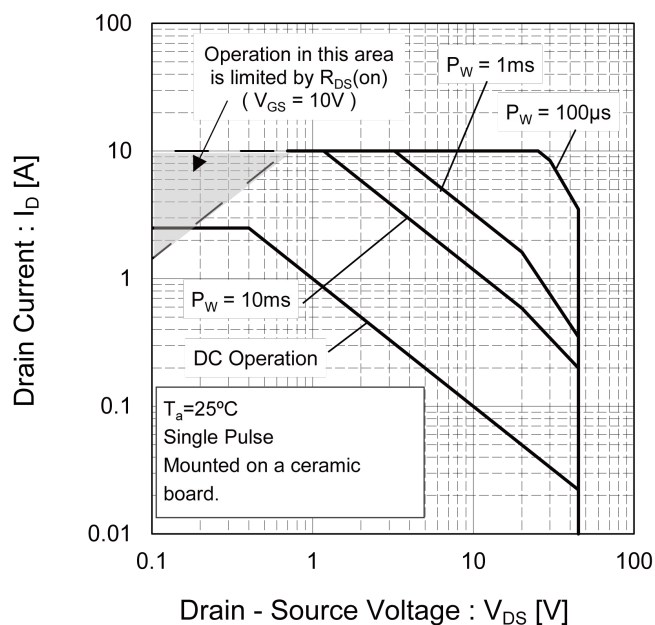


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

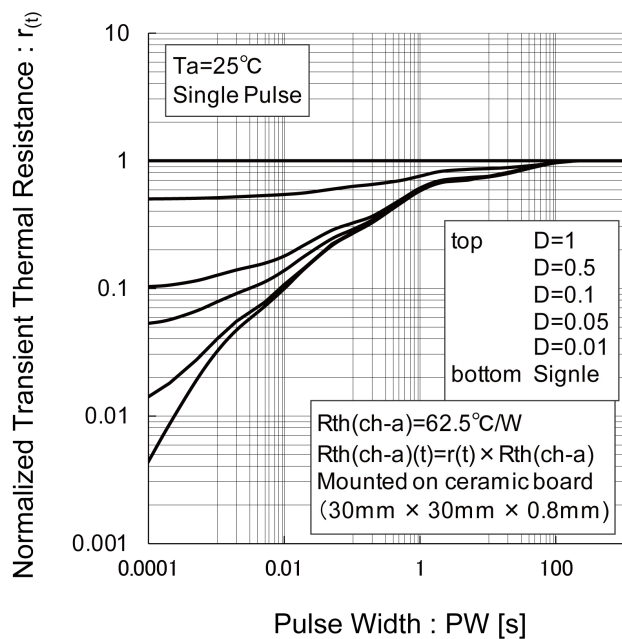
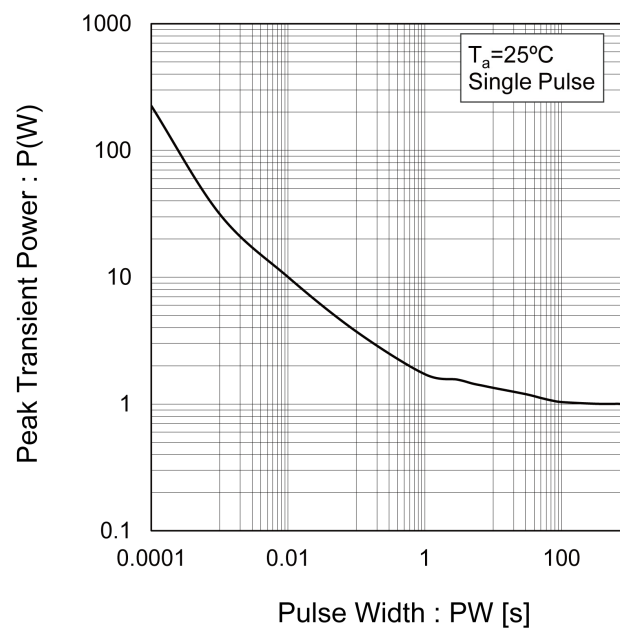


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Avalanche Current vs. Inductive Load

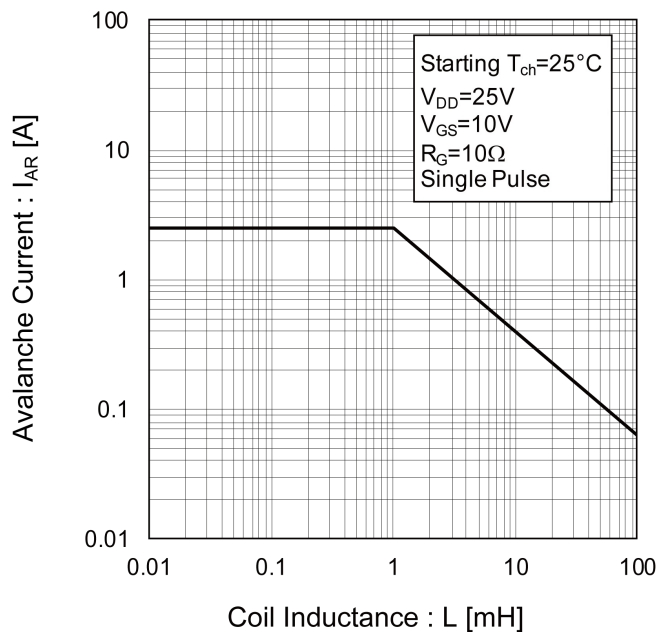


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

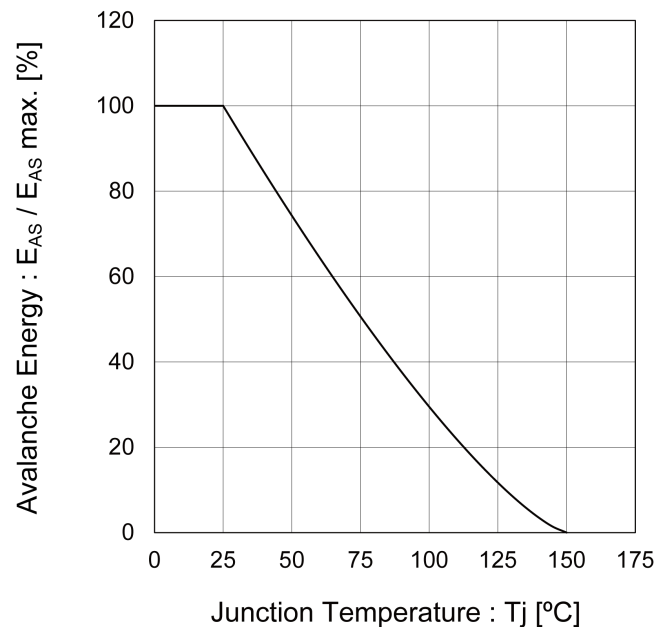


Fig.7 Typical Output Characteristics(I)

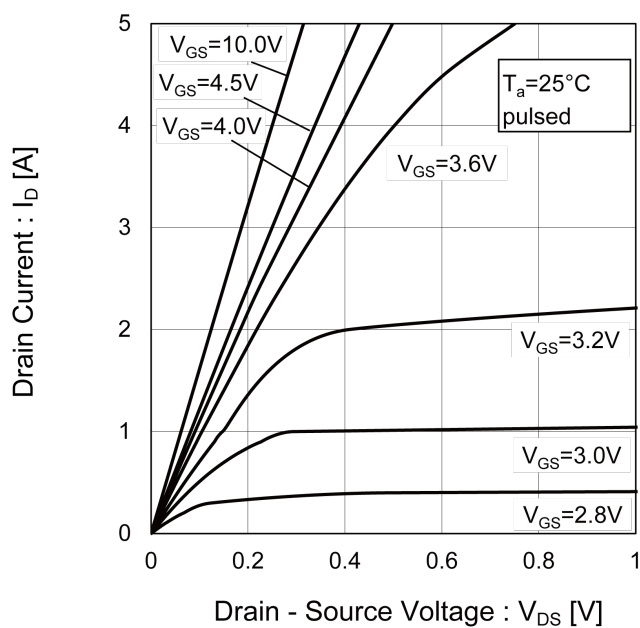
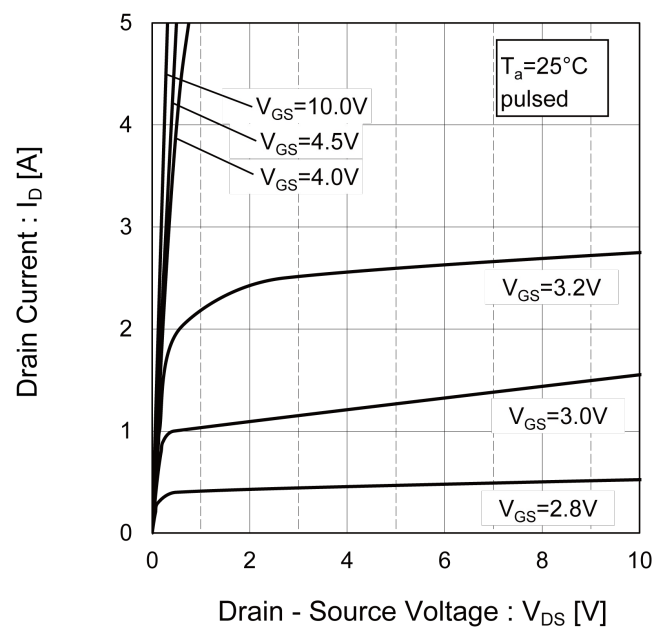


Fig.8 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.9 Breakdown Voltage vs. Junction Temperature

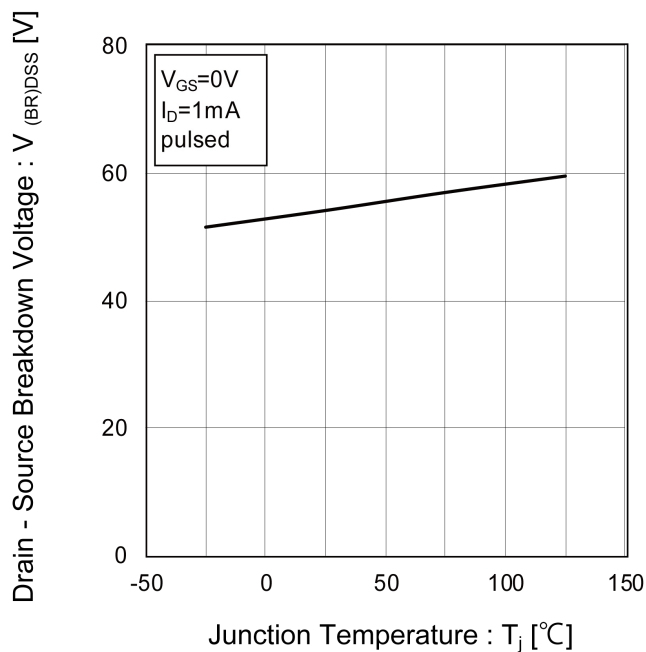


Fig.10 Typical Transfer Characteristics

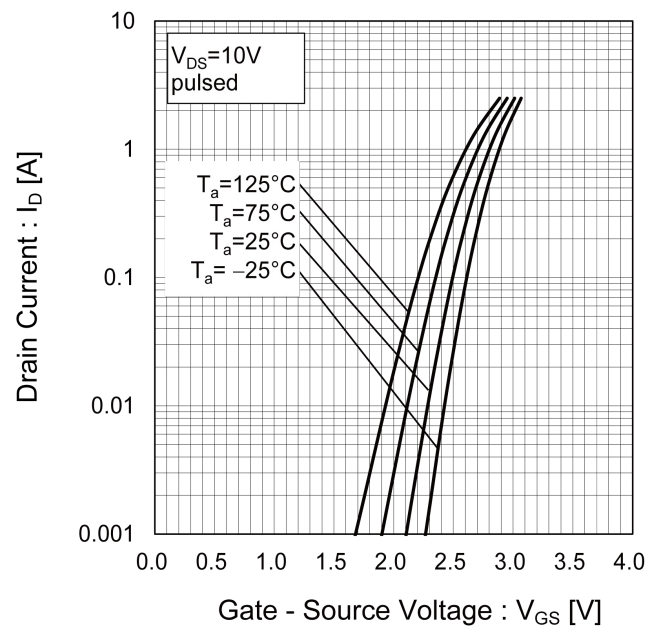


Fig.11 Gate Threshold Voltage vs. Junction Temperature

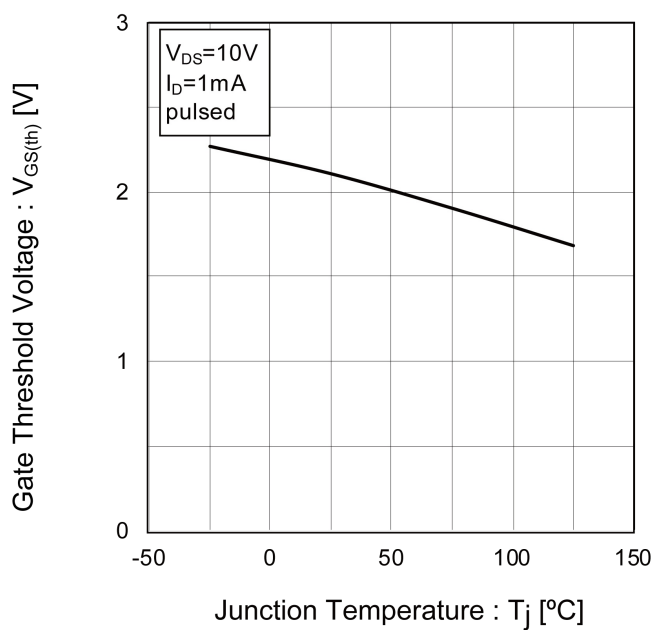
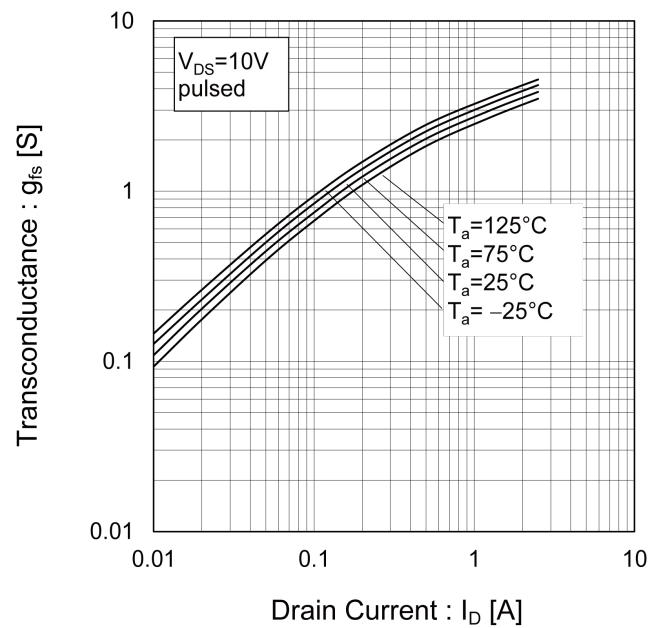


Fig.12 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.13 Drain Current Derating Curve

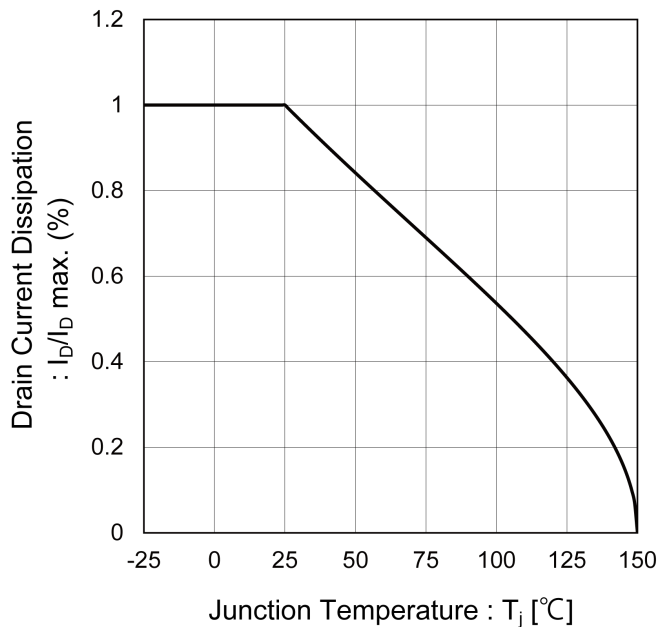


Fig.14 Static Drain - Source On - State Resistance vs. Gate Source Voltage

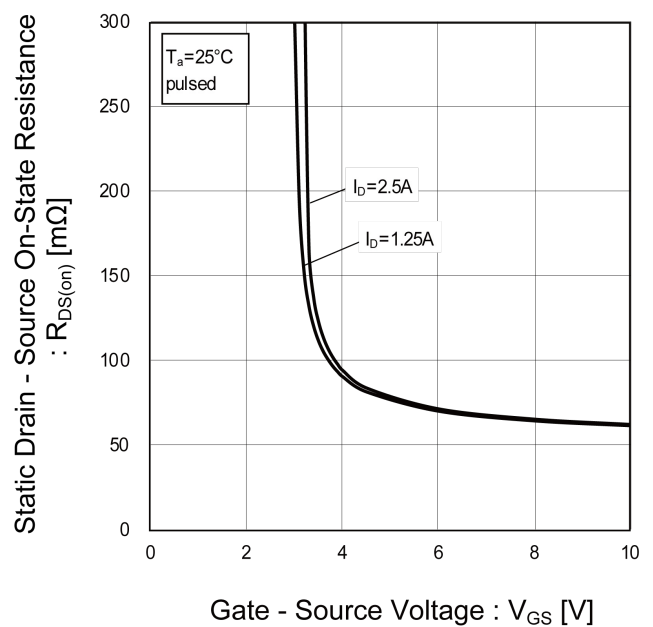


Fig.15 Static Drain - Source On - State Resistance vs. Junction Temperature

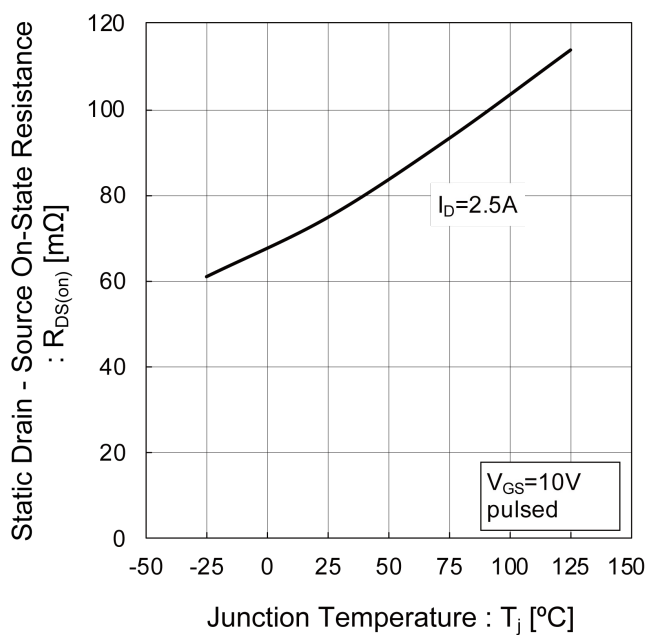
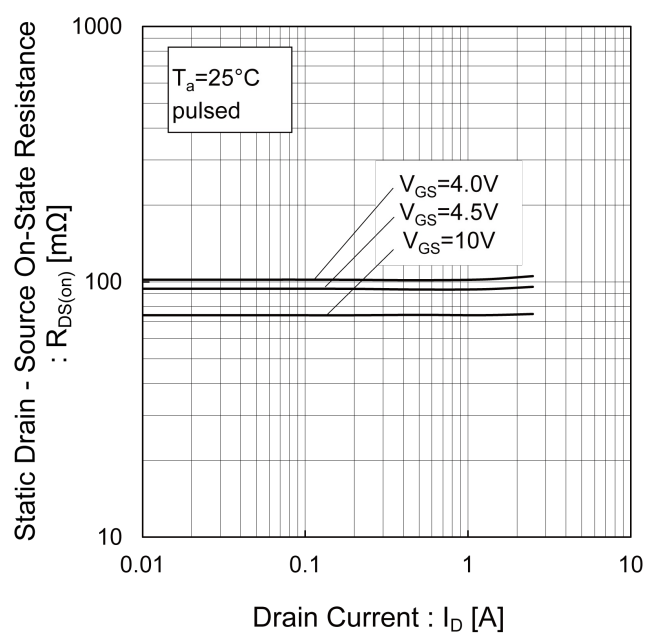


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(I)



●Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(II)

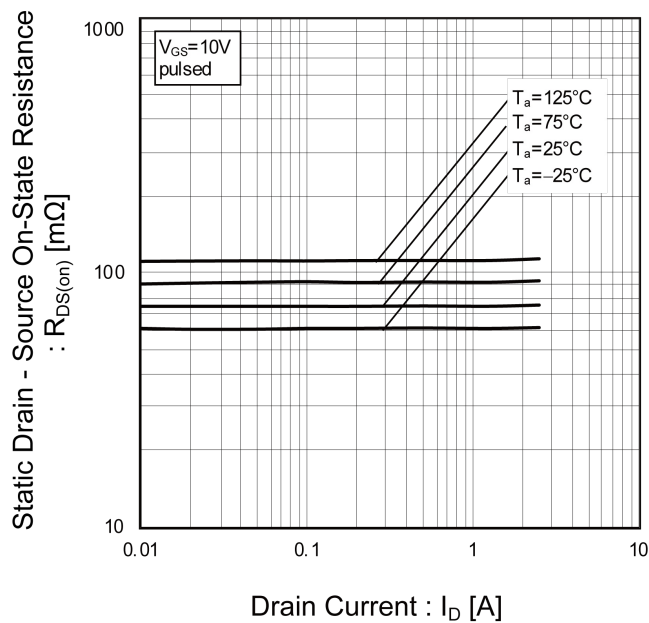


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current(III)

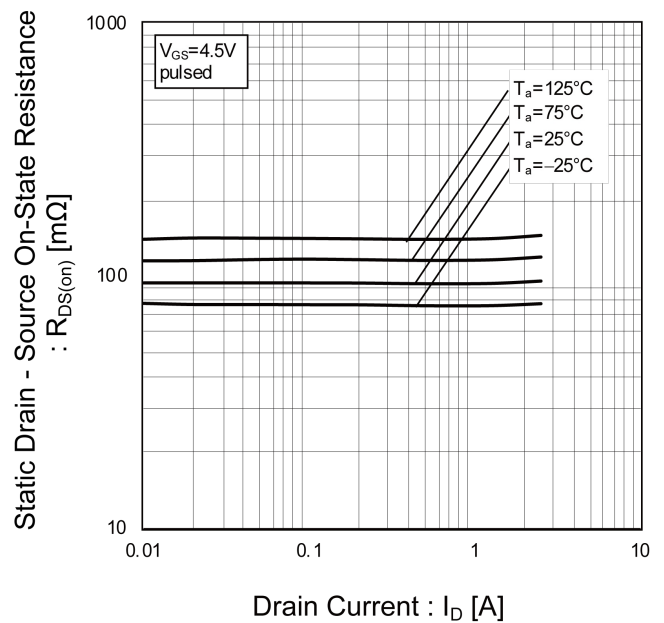
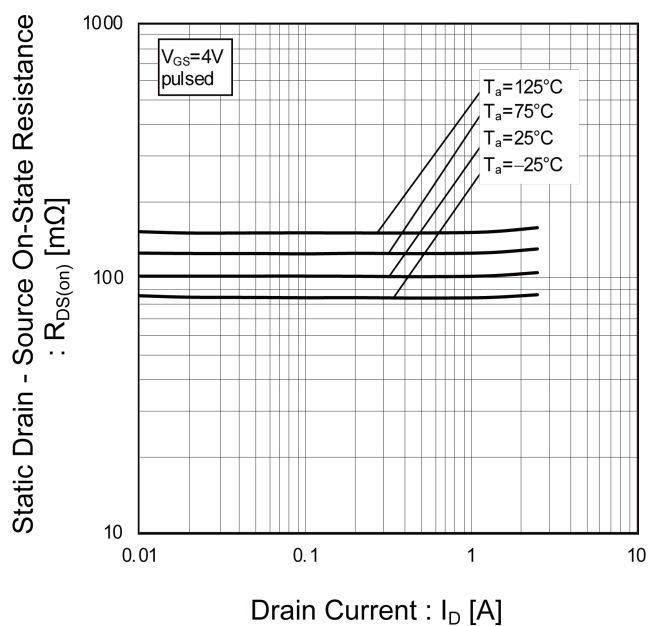


Fig.19 Static Drain - Source On - State Resistance vs. Drain Current(IV)



●Electrical characteristic curves

Fig.20 Typical Capacitance vs. Drain - Source Voltage

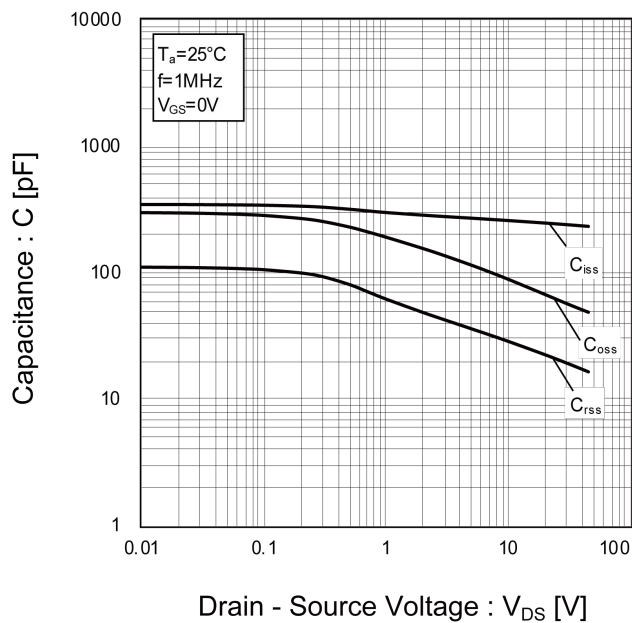


Fig.21 Switching Characteristics

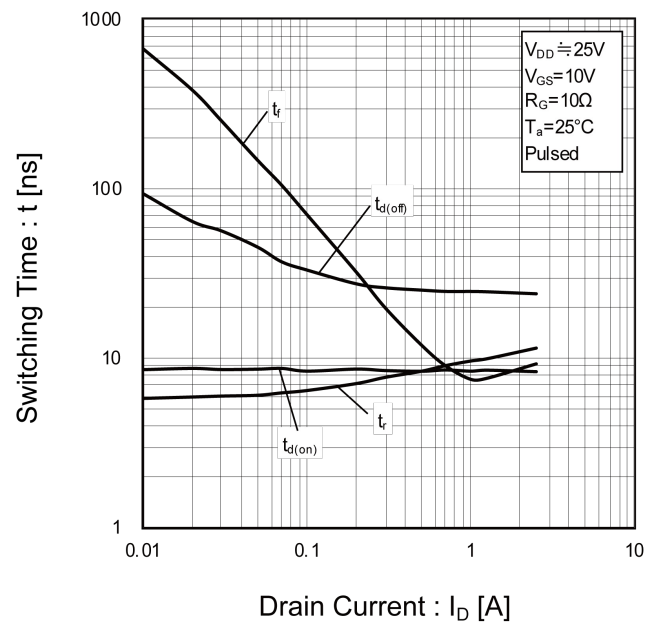


Fig.22 Dynamic Input Characteristics

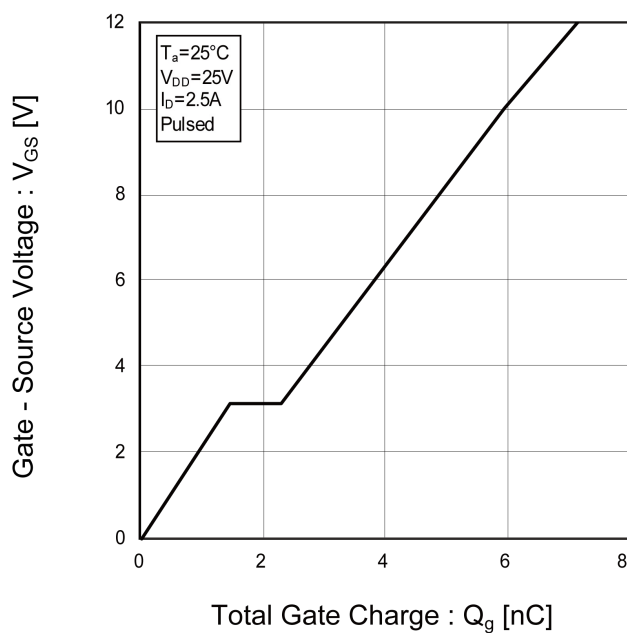
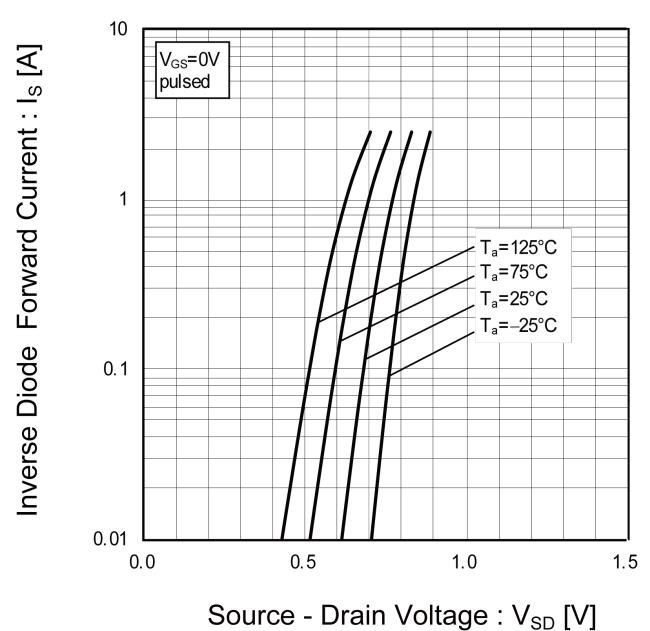


Fig.23 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

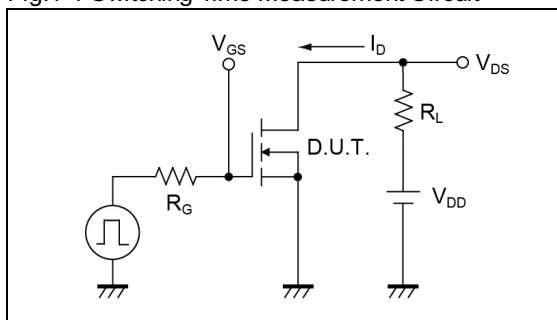


Fig.1-2 Switching Waveforms

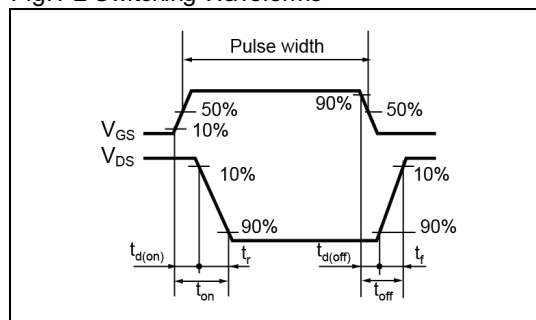


Fig.2-1 Gate Charge Measurement Circuit

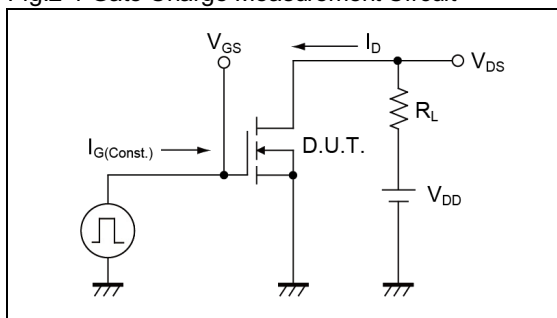


Fig.2-2 Gate Charge Waveform

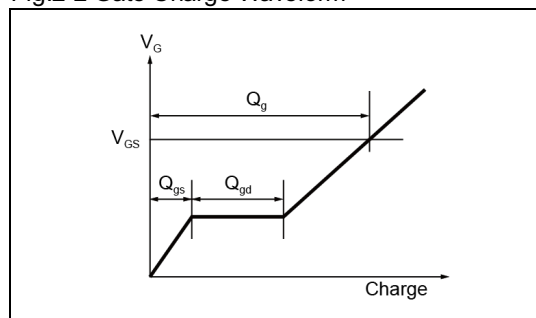


Fig.3-1 Avalanche Measurement Circuit

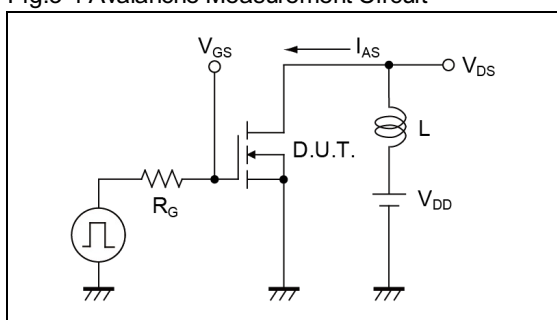
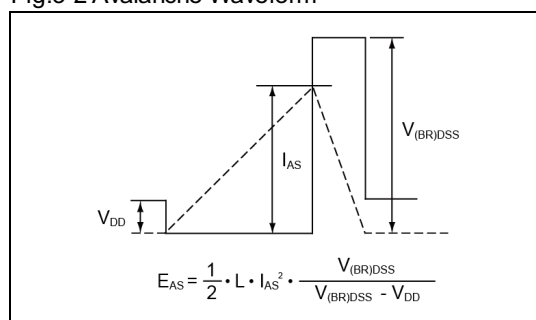
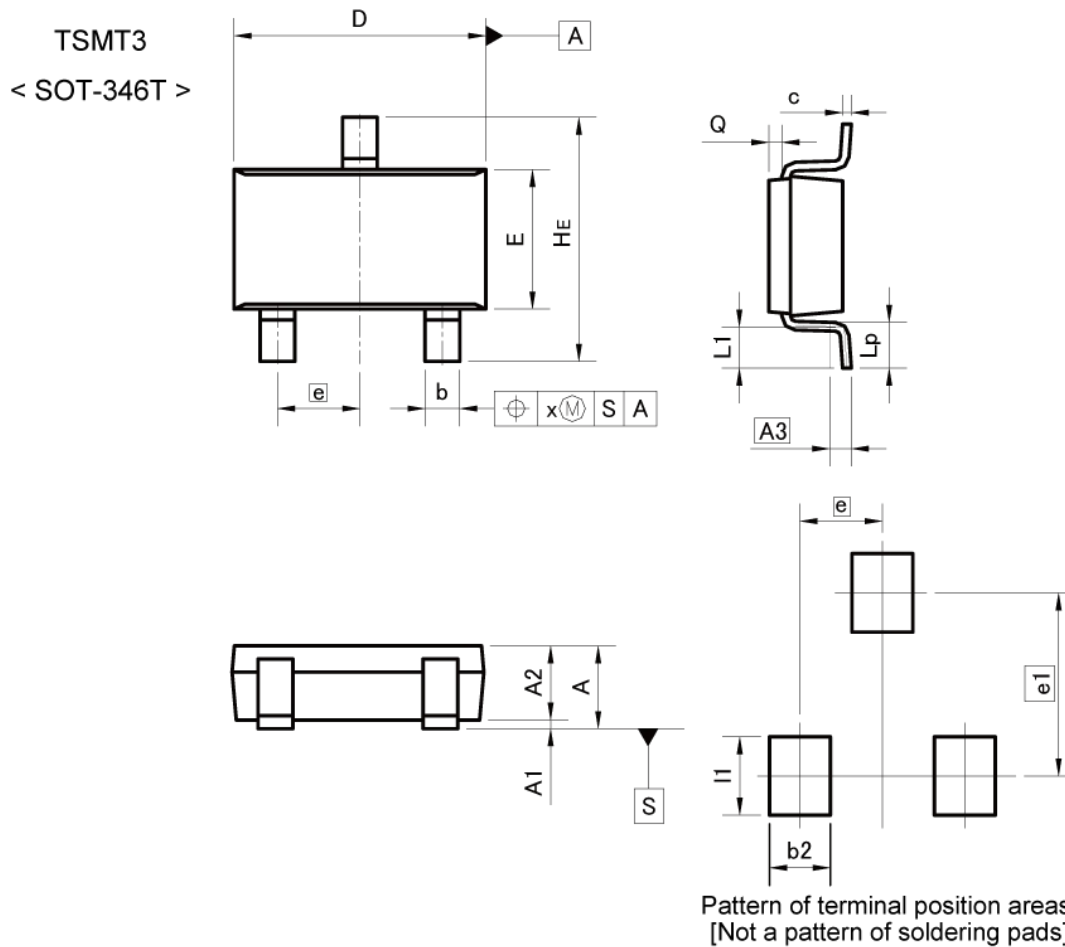


Fig.3-2 Avalanche Waveform



●Dimensions



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	1.00	—	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	—	0.20	—	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	0.70		—	0.028
e1	2.10		0.083	
l1	—	0.90	—	0.035

Dimension in mm/inches

Notes

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